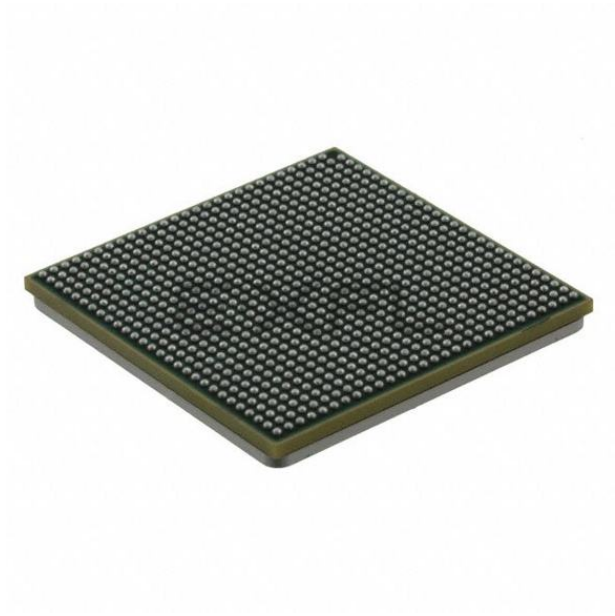

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Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Signal Processing; SPE
RAM Controllers	DDR, DDR2, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8543vtaqgb

2.1.3 Output Driver Characteristics

The following table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Programmable Output Impedance (Ω)	Supply Voltage	Notes
Local bus interface utilities signals	25 25	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	1
	45(default) 45(default)	BV_{DD} = 3.3 V BV_{DD} = 2.5 V	
PCI signals	25	OV_{DD} = 3.3 V	2
	45(default)		
DDR signal	18 36 (half strength mode)	GV_{DD} = 2.5 V	3
DDR2 signal	18 36 (half strength mode)	GV_{DD} = 1.8 V	3
TSEC/10/100 signals	45	L/TV_{DD} = 2.5/3.3 V	—
DUART, system control, JTAG	45	OV_{DD} = 3.3 V	—
I2C	150	OV_{DD} = 3.3 V	—

Notes:

1. The drive strength of the local bus interface is determined by the configuration of the appropriate bits in PORIMPSCR.
2. The drive strength of the PCI interface is determined by the setting of the $\overline{\text{PCI\_GNT1}}$ signal at reset.
3. The drive strength of the DDR interface in half-strength mode is at T_j = 105°C and at GV_{DD} (min).

2.2 Power Sequencing

The device requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power-up:

1. V_{DD}, AV_{DD}_n, BV_{DD}, LV_{DD}, OV_{DD}, SV_{DD}, TV_{DD}, XV_{DD}
2. GV_{DD}

All supplies must be at their stable values within 50 ms.

NOTE

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90% of their value before the voltage rails on the current step reach 10% of theirs.

NOTE

In order to guarantee MCKE low during power-up, the above sequencing for GV_{DD} is required. If there is no concern about any of the DDR signals being in an indeterminate state during power-up, then the sequencing for GV_{DD} is not required.

NOTE

From a system standpoint, if any of the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os associated with that I/O supply may drive a logic one or zero during power-up, and extra current may be drawn by the device.

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the device. The following table provides the RESET initialization AC timing specifications for the DDR SDRAM component(s).

Table 8. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	μs	—
Minimum assertion time for $\overline{\text{SRESET}}$	3	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	μs	—
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for all POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of $\overline{\text{HRESET}}$	—	5	SYSCLKs	1

Note:

1. SYSCLK is the primary clock input for the device.

The following table provides the PLL lock times.

Table 9. PLL Lock Times

Parameter/Condition	Min	Max	Unit
Core and platform PLL lock times	—	100	μs
Local bus PLL lock time	—	50	μs
PCI/PCI-X bus PLL lock time	—	50	μs

5.1 Power-On Ramp Rate

This section describes the AC electrical specifications for the power-on ramp rate requirements. Controlling the maximum power-on ramp rate is required to avoid falsely triggering the ESD circuitry. The following table provides the power supply ramp rate specifications.

Table 10. Power Supply Ramp Rate

Parameter	Min	Max	Unit	Notes
Required ramp rate for MVREF	—	3500	V/s	1
Required ramp rate for VDD	—	4000	V/s	1, 2

Note:

1. Maximum ramp rate from 200 to 500 mV is most critical as this range may falsely trigger the ESD circuitry.
2. VDD itself is not vulnerable to false ESD triggering; however, as per Section 22.2, "PLL Power Supply Filtering," the recommended AVDD_CORE, AVDD_PLAT, AVDD_LBIU, AVDD_PCI1 and AVDD_PCI2 filters are all connected to VDD. Their ramp rates must be equal to or less than the VDD ramp rate.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface. The DDR controller supports both DDR1 and DDR2 memories. DDR1 is supported with the following AC timings at data rates of 333 MHz. DDR2 is supported with the following AC timings at data rates down to 333 MHz.

6.2.1 DDR SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 1.8$ V.

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V

Table 17 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 2.5$ V.

Table 17. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V

This table provides the input AC timing specifications for the DDR SDRAM interface.

Table 18. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller Skew for MDQS—MDQ/MECC 533 MHz 400 MHz 333 MHz	t_{CISKEW}	 –300 –365 –390	 300 365 390	ps	1, 2

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that is captured with MDQS[n]. This must be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm (T/4 - abs(t_{CISKEW}))$ where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW}.

Table 19. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKHME}	–0.6	0.6	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[*n*] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the MDQS override bits (called WR_DATA_DELAY) in the TIMING_CFG_2 register. This is typically set to the same delay as in DDR_SDRAM_CLK_CNTL[CLK_ADJUST]. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8548E PowerQUICC III Integrated Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe must be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[*n*] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

NOTE

For the ADDR/CMD setup and hold specifications in Table 19, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.

Figure 3 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

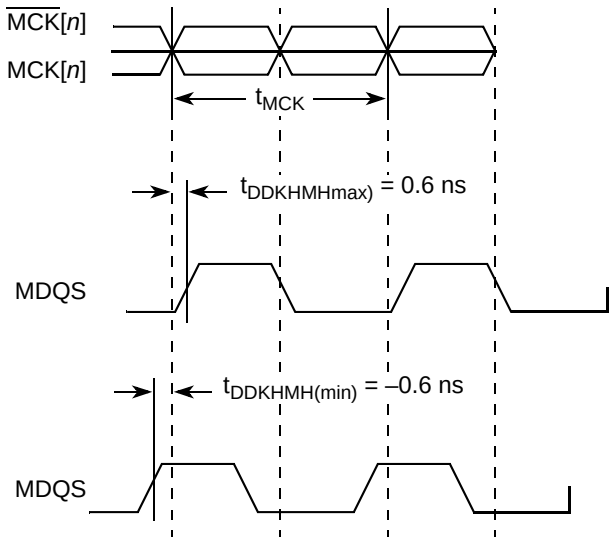

Figure 3. Timing Diagram for tDDKHMH

Figure 10 shows the GMII receive AC timing diagram.

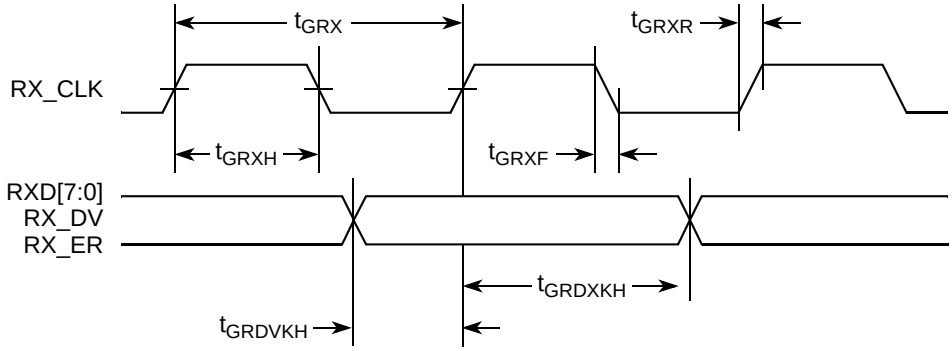

Figure 10. GMII Receive AC Timing Diagram

8.2.3 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.3.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

Table 28. MII Transmit AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}[2]	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise (20%–80%)	t_{MTXR}[2]	1.0	—	4.0	ns
TX_CLK data clock fall (80%–20%)	t_{MTXF}[2]	1.0	—	4.0	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. Guaranteed by design.

Figure 14 shows the TBI transmit AC timing diagram.

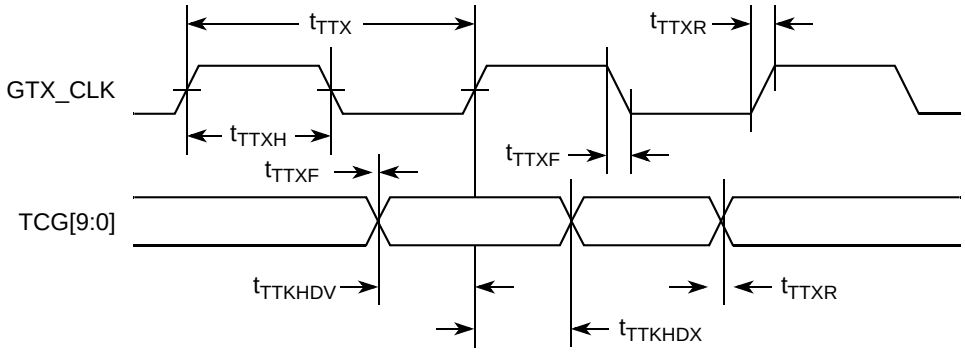

Figure 14. TBI Transmit AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

This table provides the TBI receive AC timing specifications.

Table 31. TBI Receive AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TSEC*n*_RX_CLK[0:1] clock period	t_{TRX}	—	16.0	—	ns
TSEC*n*_RX_CLK[0:1] skew	t_{SKTRX}	7.5	—	8.5	ns
TSEC*n*_RX_CLK[0:1] duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%
RCG[9:0] setup time to rising TSEC*n*_RX_CLK	t_{TRDVKH}	2.5	—	—	ns
RCG[9:0] hold time to rising TSEC*n*_RX_CLK	t_{TRDXKH}	1.5	—	—	ns
TSEC*n*_RX_CLK[0:1] clock rise time (20%–80%)	t_{TRXR}[2]	0.7	—	2.4	ns
TSEC*n*_RX_CLK[0:1] clock fall time (80%–20%)	t_{TRXF}[2]	0.7	—	2.4	ns

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Guaranteed by design.

A timing diagram for TBI receive appears in Figure 16.

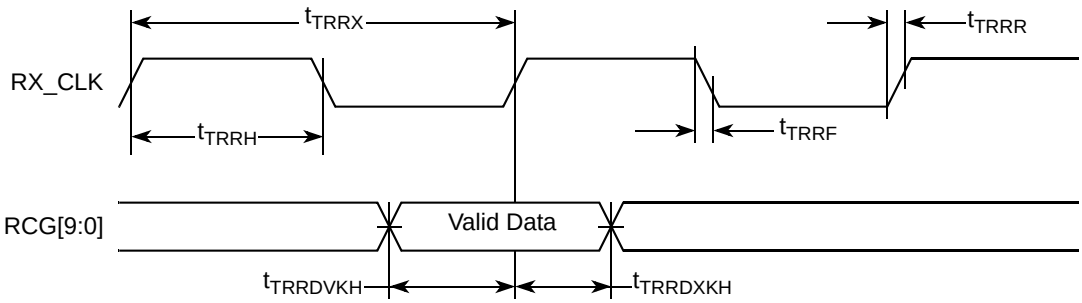

Figure 16. TBI Single-Clock Mode Receive AC Timing Diagram

8.2.6 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Table 33. RGMII and RTBI AC Timing Specifications

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}[5]	–500[6]	0	500[6]	ps
Data to clock input skew (at receiver) [2]	t_{SKRGT}	1.0	—	2.8	ns
Clock period [3]	t_{RGT}[5]	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX[3, 4]	t_{RGTH}/t_{RGT}[5]	45	50	55	%
Rise time (20%–80%)	t_{RGTR}[5]	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}[5]	—	—	0.75	ns

Notes:

1. In general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
5. Guaranteed by characterization.
6. In rev 1.0 silicon, due to errata, t_{SKRGT} is -650 ps (min) and 650 ps (max). See “eTSEC 10” in the device errata document.

9 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, RMII, TBI, and RTBI are specified in "Section 8, "Enhanced Three-Speed Ethernet (eTSEC)."

9.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.13	3.47	V
Output high voltage (OV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	OV_{DD} + 0.3	V
Output low voltage (OV_{DD} =Min, I_{OL} = 1.0 mA)	V_{OL}	GND	0.50	V
Input high voltage	V_{IH}	2.0	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current (OV_{DD} = Max, V_{IN}[1] = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 37. MII Management AC Timing Specifications

At recommended operating conditions with OV_{DD} is 3.3 V ± 5%.

Parameter	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	0.72	2.5	8.3	MHz	2, 3, 4
MDC period	t_{MDC}	120.5	—	1389	ns	—
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	—
MDC to MDIO valid	t_{MDKHDV}	$16 \times t_{CCB}$	—	—	ns	5
MDC to MDIO delay	t_{MDKHDX}	$(16 \times t_{CCB} \times 8) - 3$	—	$(16 \times t_{CCB} \times 8) + 3$	ns	5
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	—
MDC rise time	t_{MDCR}	—	—	10	ns	4

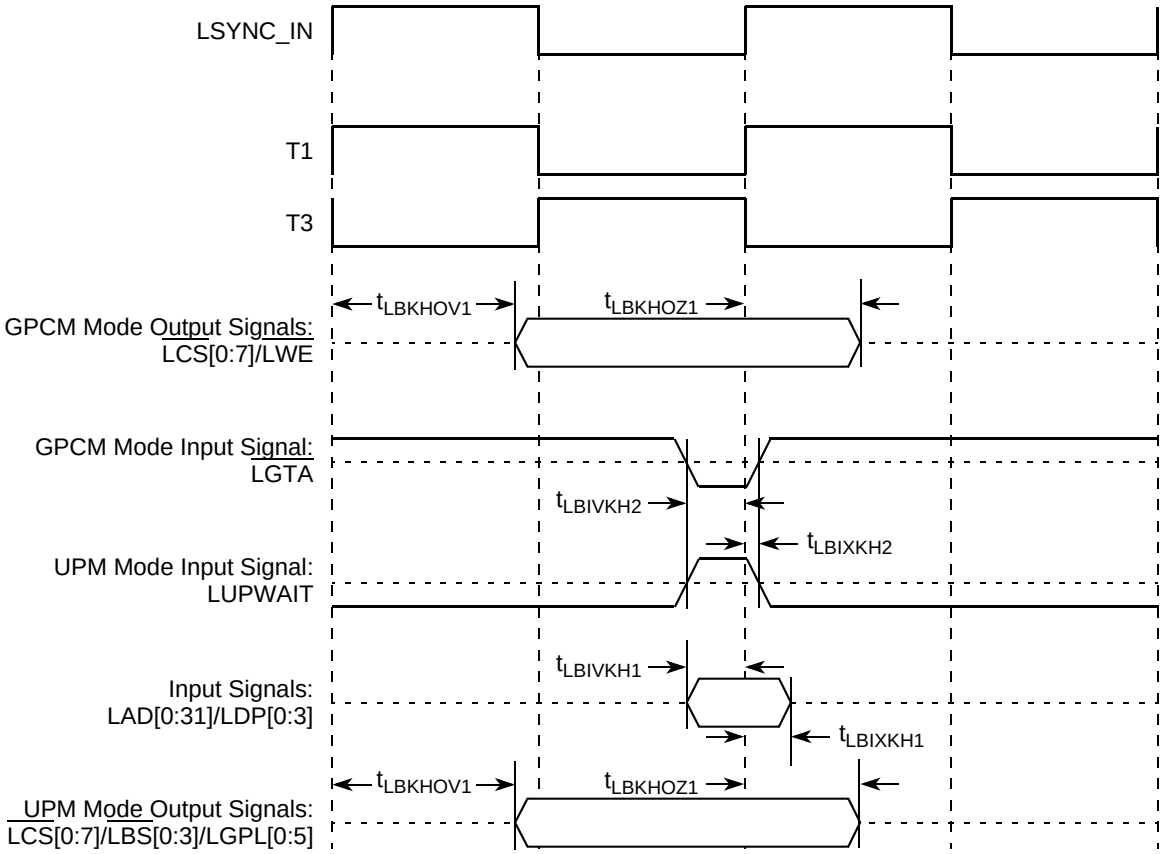

Figure 25. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (PLL Enabled)

Figure 31 provides the $\overline{\text{TRST}}$ timing diagram.

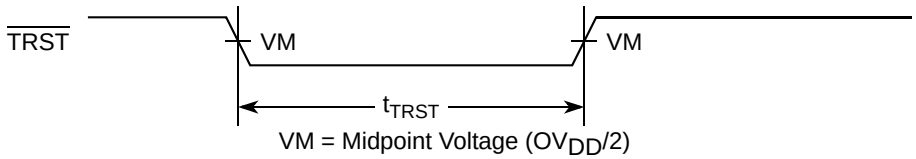

Figure 31. $\overline{\text{TRST}}$ Timing Diagram

Figure 32 provides the boundary-scan timing diagram.

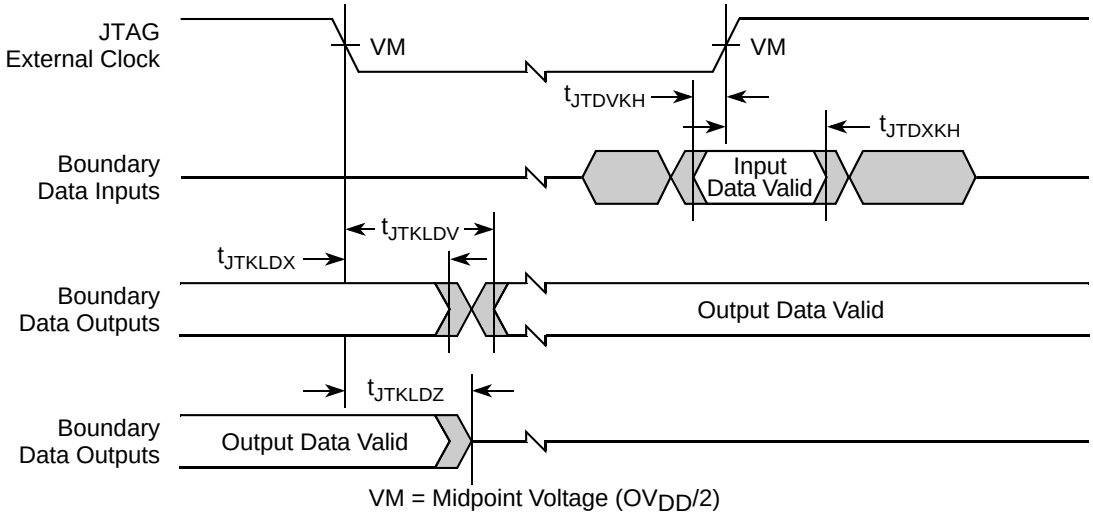

Figure 32. Boundary-Scan Timing Diagram

Figure 34 shows the AC timing diagram for the I²C bus.

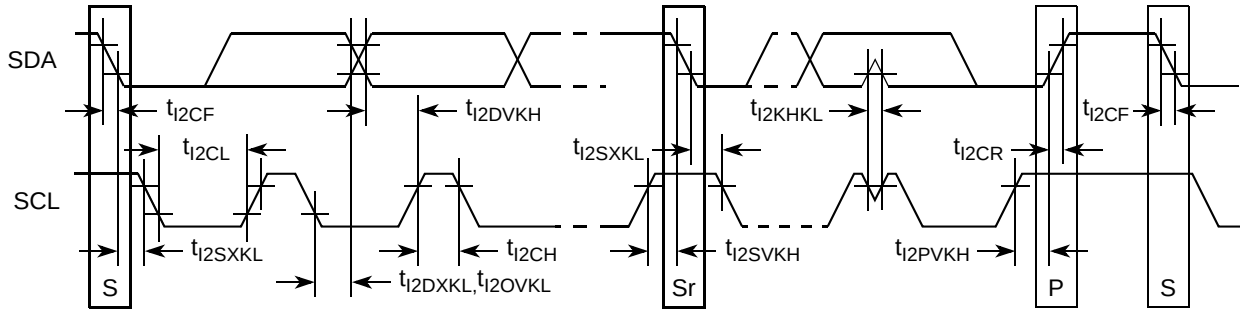

Figure 34. I²C Bus AC Timing Diagram

16 High-Speed Serial Interfaces (HSSI)

The device features one Serializer/Deserializer (SerDes) interface to be used for high-speed serial interconnect applications. The SerDes interface can be used for PCI Express and/or serial RapidIO data transfers.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes reference clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

16.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 38 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for the description. The figure shows a waveform for either a transmitter output (SD_TX and $\overline{\text{SD\_TX}}$) or a receiver input (SD_RX and $\overline{\text{SD\_RX}}$). Each signal swings between A volts and B volts where A > B.

Using this waveform, the definitions are as follows. To simplify the illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

- Single-ended swing
  The transmitter output signals and the receiver input signals SD_TX, $\overline{\text{SD\_TX}}$, SD_RX and $\overline{\text{SD\_RX}}$ each have a peak-to-peak swing of A – B volts. This is also referred as each signal wire's single-ended swing.
- Differential output voltage, V_{OD} (or differential output swing):
  The differential output voltage (or swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SD\_TX} - V_{\overline{SD\_TX}}$. The V_{OD} value can be either positive or negative.
- Differential input voltage, V_{ID} (or differential input swing):
  The differential input voltage (or swing) of the receiver, V_{ID}, is defined as the difference of the two complimentary input voltages: $V_{SD\_RX} - V_{\overline{SD\_RX}}$. The V_{ID} value can be either positive or negative.
- Differential peak voltage, V_{DIFFp}
  The peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak voltage, $V_{DIFFp} = |A - B|$ volts.
- Differential peak-to-peak, $V_{DIFFp-p}$
  Because the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak-to-peak voltage, $V_{DIFFp-p} = 2 \times V_{DIFFp} = 2 \times |(A - B)|$ volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-to-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2 \times |V_{OD}|$.
- Common mode voltage, V_{cm}
  The common mode voltage is equal to one half of the sum of the voltages between each conductor

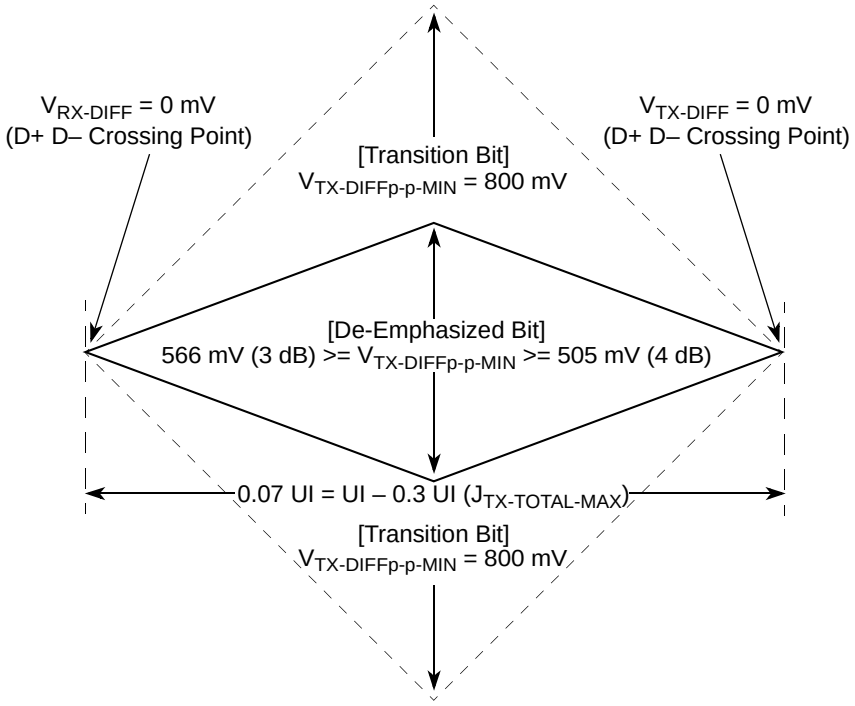

Figure 48. Minimum Transmitter Timing and Voltage Output Compliance Specifications

17.4.3 Differential Receiver (RX) Input Specifications

Table 57 defines the specifications for the differential input at all receivers (RXs). The parameters are specified at the component pins.

Table 57. Differential Receiver (RX) Input Specifications

Symbol	Parameter	Min	Nom	Max	Unit	Comments
UI	Unit interval	399.88	400	400.12	ps	Each UI is 400 ps ± 300 ppm. UI does not account for spread spectrum clock dictated variations. See Note 1.
$V_{RX-DIFFp-p}$	Differential peak-to-peak input voltage	0.175	—	1.200	V	$V_{RX-DIFFp-p} = 2 \times \lvert V_{RX-D+} - V_{RX-D-}\rvert$. See Note 2.
T_{RX-EYE}	Minimum receiver eye width	0.4	—	—	UI	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 - T_{RX-EYE} = 0.6$ UI. See Notes 2 and 3.
$T_{RX-EYE-MEDIAN-to-MAX-JITTER}$	Maximum time between the jitter median and maximum deviation from the median	—	—	0.3	UI	Jitter is defined as the measurement variation of the crossing points ($V_{RX-DIFFp-p}$ = 0 V) in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI. See Notes 2, 3, and 7.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.

NOTE

The reference impedance for return loss measurements is 50. to ground for both the D+ and D– line (that is, as measured by a vector network analyzer with 50-Ω probes—see Figure 50). Note that the series capacitors, CTX, are optional for the return loss measurement.

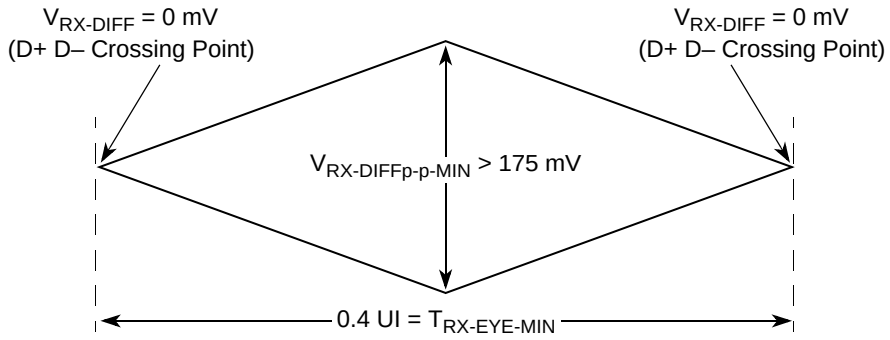

Figure 49. Minimum Receiver Eye Timing and Voltage Compliance Specification

17.5.1 Compliance Test and Measurement Load

The AC timing and voltage parameters must be verified at the measurement point, as specified within 0.2 inches of the package pins, into a test/measurement load shown in Figure 50.

NOTE

The allowance of the measurement point to be within 0.2 inches of the package pins is meant to acknowledge that package/board routing may benefit from D+ and D– not being exactly matched in length at the package pin boundary.

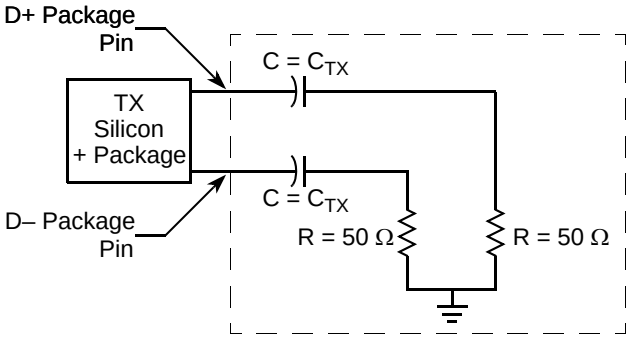

Figure 50. Compliance Test/Measurement Load

transmitter that implements pre-emphasis (to equalize the link and reduce inter-symbol interference) need only comply with the transmitter output compliance mask when pre-emphasis is disabled or minimized.

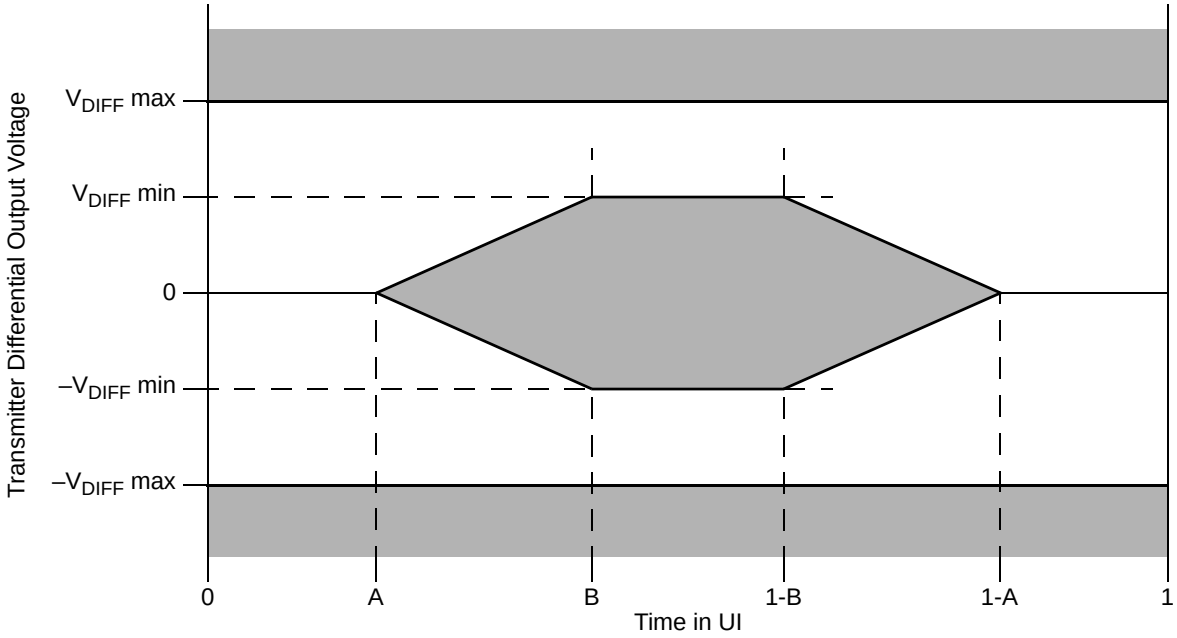

Figure 52. Transmitter Output Compliance Mask

Table 65. Transmitter Differential Output Eye Diagram Parameters

Transmitter Type	V_{DIFF}min (mV)	V_{DIFF}max (mV)	A (UI)	B (UI)
1.25 GBaud short range	250	500	0.175	0.39
1.25 GBaud long range	400	800	0.175	0.39
2.5 GBaud short range	250	500	0.175	0.39
2.5 GBaud long range	400	800	0.175	0.39
3.125 GBaud short range	250	500	0.175	0.39
3.125 GBaud long range	400	800	0.175	0.39

18.7 Receiver Specifications

LP-serial receiver electrical and timing specifications are stated in the text and tables of this section.

Receiver input impedance shall result in a differential return loss better that 10 dB and a common mode return loss better than 6 dB from 100 MHz to (0.8) × (baud frequency). This includes contributions from on-chip circuitry, the chip package, and any off-chip components related to the receiver. AC coupling

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_FRAME	AE11	I/O	OV_{DD}	2
PCI1_IDSEL	AG9	I	OV_{DD}	—
PCI1_REQ64/PCI2_FRAME	AF14	I/O	OV_{DD}	2, 5, 10
PCI1_ACK64/PCI2_DEVSEL	V15	I/O	OV_{DD}	2
PCI2_CLK	AE28	I	OV_{DD}	39
PCI2_IRDY	AD26	I/O	OV_{DD}	2
PCI2_PERR	AD25	I/O	OV_{DD}	2
PCI2_GNT[4:1]	AE26, AG24, AF25, AE25	O	OV_{DD}	5, 9, 35
PCI2_GNT0	AG25	I/O	OV_{DD}	—
PCI2_SERR	AD24	I/O	OV_{DD}	2,4
PCI2_STOP	AF24	I/O	OV_{DD}	2
PCI2_TRDY	AD27	I/O	OV_{DD}	2
PCI2_REQ[4:1]	AD28, AE27, W17, AF26	I	OV_{DD}	—
PCI2_REQ0	AH25	I/O	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	L18, J18, K14, L13, L19, M18, L15, L14, A17, B17, A13, B12, C18, B18, B13, A12, H18, F18, J14, F15, K19, J19, H16, K15, D17, G16, K13, D14, D18, F17, F14, E14, A7, A6, D5, A4, C8, D7, B5, B4, A2, B1, D1, E4, A3, B2, D2, E3, F3, G4, J5, K5, F6, G5, J6, K4, J1, K2, M5, M3, J3, J2, L1, M6	I/O	GV_{DD}	—
MECC[0:7]	H13, F13, F11, C11, J13, G13, D12, M12	I/O	GV_{DD}	—
MDM[0:8]	M17, C16, K17, E16, B6, C4, H4, K1, E13	O	GV_{DD}	—
MDQS[0:8]	M15, A16, G17, G14, A5, D3, H1, L2, C13	I/O	GV_{DD}	—
MDQS[0:8]	L17, B16, J16, H14, C6, C2, H3, L4, D13	I/O	GV_{DD}	—
MA[0:15]	A8, F9, D9, B9, A9, L10, M10, H10, K10, G10, B8, E10, B10, G6, A10, L11	O	GV_{DD}	—
MBA[0:2]	F7, J7, M11	O	GV_{DD}	—
MWE	E7	O	GV_{DD}	—
MCAS	H7	O	GV_{DD}	—
MRAS	L8	O	GV_{DD}	—
MCKE[0:3]	F10, C10, J11, H11	O	GV_{DD}	11
MCS[0:3]	K8, J8, G8, F8	O	GV_{DD}	—
MCK[0:5]	H9, B15, G2, M9, A14, F1	O	GV_{DD}	—
MCK[0:5]	J9, A15, G1, L9, B14, F2	O	GV_{DD}	—
MODT[0:3]	E6, K6, L7, M7	O	GV_{DD}	—

Table 73. MPC8545E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{UDE}}$	AH16	I	OV_{DD}	—
$\overline{\text{MCP}}$	AG19	I	OV_{DD}	—
IRQ[0:7]	AG23, AF18, AE18, AF20, AG18, AF17, AH24, AE20	I	OV_{DD}	—
IRQ[8]	AF19	I	OV_{DD}	—
IRQ[9]/$\overline{\text{DMA\_DREQ3}}$	AF21	I	OV_{DD}	1
IRQ[10]/$\overline{\text{DMA\_DACK3}}$	AE19	I/O	OV_{DD}	1
IRQ[11]/$\overline{\text{DMA\_DDONE3}}$	AD20	I/O	OV_{DD}	1
$\overline{\text{IRQ\_OUT}}$	AD18	O	OV_{DD}	2, 4
Ethernet Management Interface				
EC_MDC	AB9	O	OV_{DD}	5, 9
EC_MDIO	AC8	I/O	OV_{DD}	—
Gigabit Reference Clock				
EC_GTX_CLK125	V11	I	LV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_RXD[7:0]	R5, U1, R3, U2, V3, V1, T3, T2	I	LV_{DD}	—
TSEC1_TXD[7:0]	T10, V7, U10, U5, U4, V6, T5, T8	O	LV_{DD}	5, 9
TSEC1_COL	R4	I	LV_{DD}	—
TSEC1_CRS	V5	I/O	LV_{DD}	20
TSEC1_GTX_CLK	U7	O	LV_{DD}	—
TSEC1_RX_CLK	U3	I	LV_{DD}	—
TSEC1_RX_DV	V2	I	LV_{DD}	—
TSEC1_RX_ER	T1	I	LV_{DD}	—
TSEC1_TX_CLK	T6	I	LV_{DD}	—
TSEC1_TX_EN	U9	O	LV_{DD}	30
TSEC1_TX_ER	T7	O	LV_{DD}	—
GPIN[0:7]	P2, R2, N1, N2, P3, M2, M1, N3	I	LV_{DD}	103
GPOUT[0:5]	N9, N10, P8, N7, R9, N5	O	LV_{DD}	—
cfg_dram_type0/GPOUT6	R8	O	LV_{DD}	5, 9
GPOUT7	N6	O	LV_{DD}	—
Reserved	P1	—	—	104
Reserved	R6	—	—	104
Reserved	P6	—	—	15
Reserved	N4	—	—	105

20 Clocking

This section describes the PLL configuration of the device. Note that the platform clock is identical to the core complex bus (CCB) clock.

20.1 Clock Ranges

Table 75 through Table 77 provide the clocking specifications for the processor cores and Table 78, through Table 80 provide the clocking specifications for the memory bus.

Table 75. Processor Core Clocking Specifications (MPC8548E and MPC8547E)

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	1000 MHz		1200 MHz		1333 MHz			
	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	800	1000	800	1200	800	1333	MHz	1, 2

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.

2.)The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 76. Processor Core Clocking Specifications (MPC8545E)

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	800 MHz		1000 MHz		1200 MHz			
	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	800	800	800	1000	800	1200	MHz	1, 2

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.

2.)The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 77. Processor Core Clocking Specifications (MPC8543E)

Characteristic	Maximum Processor Core Frequency				Unit	Notes
	800 MHz		1000 MHz			
	Min	Max	Min	Max		
e500 core processor frequency	800	800	800	1000	MHz	1, 2

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.

2.)The minimum e500 core frequency is based on the minimum platform frequency of 333 MHz.

Table 78. Memory Bus Clocking Specifications (MPC8548E and MPC8547E)

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	1000, 1200, 1333 MHz			
	Min	Max		
Memory bus clock speed	166	266	MHz	1, 2

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.

Table 79. Memory Bus Clocking Specifications (MPC8545E)

Characteristic	Maximum Processor Core Frequency		Unit	Notes
	800, 1000, 1200 MHz			
	Min	Max		
Memory bus clock speed	166	200	MHz	1, 2

Notes:

1. **Caution:** The CCB clock to SYSCLK ratio and e500 core to CCB clock ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB clock frequency do not exceed their respective maximum or minimum operating frequencies. See Section 20.2, “CCB/SYSCLK PLL Ratio,” and Section 20.3, “e500 Core PLL Ratio,” for ratio settings.
2. The memory bus speed is half of the DDR/DDR2 data rate, hence, half of the platform clock frequency.